

Silicon NPN Power Transistors

2N6372 2N6373 2N6374

DESCRIPTION

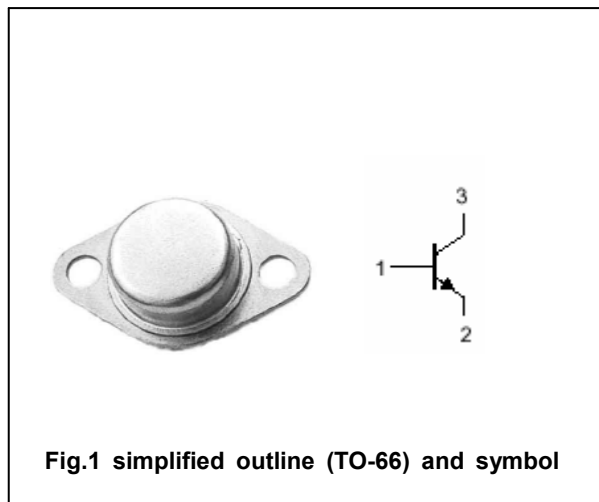
- With TO-66 package
- Low collector saturation voltage
- Excellent safe operating area

APPLICATIONS

- Designed for switching and wide-band amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6372	90	V
		2N6373	70	
		2N6374	50	
V _{CEO}	Collector-emitter voltage	2N6372	80	V
		2N6373	60	
		2N6374	40	
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		6	A
P _D	Total Power Dissipation	T _C =25□	40	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	4.37	□/W

Silicon NPN Power Transistors

2N6372 2N6373 2N6374

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CE0(SUS)}	Collector-emitter sustaining voltage	2N6372	I _C =0.1A ; I _B =0	80			V
		2N6373		60			
		2N6374		40			
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =2A; I _B =0.2A			0.7	V	
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =6A; I _B =0.6A			1.2	V	
V _{BEsat-1}	Base-emitter saturation voltage	I _C =2A; I _B =0.2A			1.2	V	
V _{BEsat-2}	Base-emitter saturation voltage	I _C =6A; I _B =0.6A			2.0	V	
I _{CEO}	Collector cut-off current	2N6372	V _{CE} =80V; I _B =0			0.1	mA
		2N6373		V _{CE} =60V; I _B =0			
		2N6374		V _{CE} =40V; I _B =0			
I _{CBO}	Collector cut-off current	V _{CB} =Rated V _{CB} ; I _E =0			10	μA	
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			0.1	mA	
h _{FE}	DC current gain	2N6372	I _C =2A ; V _{CE} =2V	20	100		
		2N6373					I _C =2.5A ; V _{CE} =2V
		2N6374					I _C =3A ; V _{CE} =2V
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V; f=1MHz		4		MHz	

Silicon NPN Power Transistors

2N6372 2N6373 2N6374

PACKAGE OUTLINE

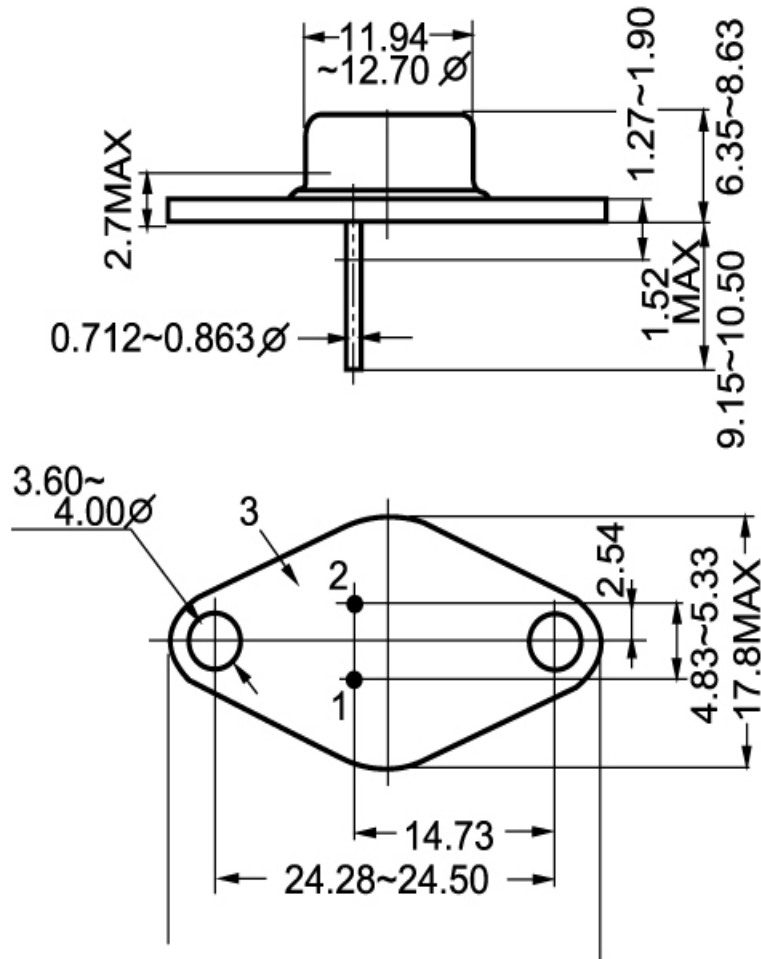


Fig.2 outline dimensions